

Please add the following new claims:

- 11. (New) An electric semiconductor component, comprising:
a monocrystalline semiconductor substrate;
an insulation layer arranged on a surface of the semiconductor substrate and penetrated by at least one contact hole in at least one location; and
a contact structure that contacts the semiconductor substrate through the contact hole and made of a material in which a semiconductor material of the semiconductor substrate is soluble in an anisotropic dissolving process;
wherein edges of the contact hole include diffusion stop structures.
12. (New) The semiconductor component according to claim 11, wherein the diffusion stop structures include curved segments.
13. (New) The semiconductor component according to claim 12, wherein the contact hole is shaped one of circular and as overlapping intersecting circles.
- 92 14. (New) The semiconductor component according to claim 11, wherein the diffusion stop structures include microstructured sections of the edges.
15. (New) The semiconductor component according to claim 14, wherein the microstructured sections include one of a crenellated and a sawtooth pattern.
16. (New) The semiconductor component according to claim 15, wherein the one of the crenellated and the sawtooth pattern includes a plurality of projections, each projection having an edge length of at most 2 μm .
17. (New) The semiconductor component according to claim 11, wherein the semiconductor material includes at least one class of crystal planes that is subject to one of little and no attack in the dissolving process, and the diffusion stop structures include rectilinear sections of the edges intersecting the crystal planes of the class of crystal planes extending in the semiconductor substrate beneath the contact hole.